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11/13/02

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Gu, Allman  
Serial Number: 09/878,820  
Filed: 2001.06.11  
Title: Plasma Treatment System  
Examiner: DuyVu n Deo  
Group Art Unit: 1765  
Attorney Docket: 01-096

## AMENDMENT A

Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington DC 20231

Via Fax at 1.703.872.9310

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GROUP 1700

OFFICIAL

Sir:

In response to the office action dated 2002.08.12, please amend the above-referenced application as follows:

## IN THE CLAIMS

1. (amended) A process for forming a conductive via in an integrated circuit structure, where the integrated circuit structure includes a first dielectric layer overlying a first conductive layer, the process comprising:
- (a) forming a via cavity in the first dielectric layer, the via cavity exposing the first conductive layer;
  - (b) etching the via cavity with a hydrogen-containing plasma;
  - (c) forming a liner layer in the via cavity;
  - (d) exposing the liner layer to an isotropic plasma of hydrogen and nitrogen ions, thereby densifying the liner layer, including sidewalls of the liner layer, and
  - (e) forming a second conductive layer adjacent the liner layer in the via cavity, the second conductive layer substantially filling the via cavity to form the conductive via.

Please cancel claim 6 without prejudice or disclaimer.